

# P-Channel Enhancement Mode MOSFET

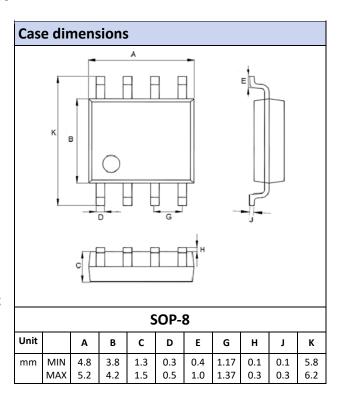
| Primary characteristics |                                       |       |           |  |  |
|-------------------------|---------------------------------------|-------|-----------|--|--|
| Symbol                  | Parameter                             | Value | Unit      |  |  |
| I <sub>D</sub>          | Continuous drain current              | 4.0   | Α         |  |  |
| $V_{\text{DSS}}$        | Drain source voltage                  | 60    | V         |  |  |
| R <sub>DSON</sub>       | Static drain-source on-<br>resistance | 135   | mΩ<br>MAX |  |  |

#### **Features**

- SOP-8 case for easy automatic insertion
- Pb-free and RoHS compliant
- High density cell design for ultralow R<sub>DS(ON)</sub>
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Molding compound: UL Flammability Classification Rating 94V-0
- Terminals: matte tin-plated leads; solderability-per MIL-STD-202, Method 208

# **Applications**

- Power switching applications
- Hard switched and high frequency circuits
- Uninterruptible power supply



| Maximum ratings (T <sub>A</sub> = 25°C unless otherwise noted) |                                   |           |      |  |  |  |  |
|--|-----------------------------------|-----------|------|--|--|--|--|
| Characteristic   | Symbol                            | Value     | Unit |  |  |  |  |
| Drain-source voltage   | V <sub>DSS</sub>                  | 60        | V    |  |  |  |  |
| Gate-source voltage  | V <sub>GSS</sub>                  | ±20       | V    |  |  |  |  |
| Continuous drain current (T <sub>C</sub> =25°C)                | ID                                | 4.0       | А    |  |  |  |  |
| Pulsed drain current <sup>2)</sup>                             | I <sub>DM</sub>                   | 20        | Α    |  |  |  |  |
| Power Dissipation  | P <sub>D</sub>                    | 1.6       | W    |  |  |  |  |
| Operating junction temperature range                           | T <sub>J</sub> , T <sub>STG</sub> | -55 ~ 150 | °C   |  |  |  |  |

| Thermal characteristics                |                |                  |       |      |      |      |
|--|----------------|------------------|-------|------|------|------|
| Characteristic                         | Tost soudition | Symbol           | Value |      |      | Unit |
| Characteristic                         | Test condition |                  | Min.  | Тур. | Max. | Uill |
| Thermal resistance junction-ambient 1) | -              | R <sub>eJA</sub> | -     | 78   | -    | °C/W |

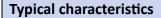


| Electrical characteristics (T <sub>A</sub> = 25°C) |  |                     | 1     |      |      |       |
|--|--|---------------------|-------|------|------|-------|
| Characteristic                                     | Test condition   | Symbol              | Value |      |      | Unit  |
| Characteristic                                     |  |                     | Min.  | Тур. | Max. | Jilit |
| Drain-source breakdown voltage                     | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA               | V <sub>DSS</sub>    | 60    | -    | -    | V     |
| Zero gate voltage drain current                    | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                | I <sub>DSS</sub>    | -     | -    | 1.0  | μΑ    |
| Gate body leakage current                          | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V               | I <sub>GSS</sub>    | -     | -    | ±100 | nA    |
| Gate threshold voltage 3)                          | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250yA | $V_{GS(TH)}$        | 1.0   | 1.6  | 3.0  | V     |
| Drain-source on-state resistance 3)                | V <sub>GS</sub> =10V, I <sub>D</sub> =4.0A               | D                   | -     | 70   | 90   | mΩ    |
| Drain-source on-state resistance -/                | V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.0A              | R <sub>DS(ON)</sub> | -     | 100  | 135  |       |
| Dynamic electrical characteristics 4)              |  |                     |       |      |      |       |
|  | <b>-</b>   |                     | Value |      |      |       |
| Characteristic                                     | Test condition   | Symbol              | Min.  | Тур. | Max. | Unit  |
| Forward transconductance                           | V <sub>DS</sub> =5.0V, I <sub>D</sub> =4.0A              | grs                 | -     | 10   | -    | S     |
| Input capacitance                                  | V <sub>DS</sub> =30V                                     | Cıss                | -     | 930  | -    |       |
| Output capacitance                                 | V <sub>GS</sub> =0V                                      | Coss                | -     | 55   | -    | pF    |
| Reverse transfer capacitance                       | f=1.0MHz   | C <sub>RSS</sub>    | -     | 41   | -    |       |
| Turn ON delay time                                 | V <sub>DS</sub> =30V                                     | t <sub>d(ON)</sub>  | -     | 8.0  | -    |       |
| Turn ON rise time                                  | V <sub>GS</sub> =10V                                     | tr                  | -     | 4.0  | -    |       |
| Turn OFF delay time                                | R <sub>G</sub> =3.0Ω                                     | t <sub>d(OFF)</sub> | -     | 32   | -    | ns    |
| Turn OFF fall time                                 | R <sub>L</sub> =7.5Ω                                     | t <sub>f</sub>      | -     | 7.0  | -    |       |
| Switching characteristics 4)                       |  |                     |       |      |      |       |
|  |  | Symbol              | Value |      | Ī ,  |       |
| Characteristic                                     | Test condition   |                     | Min.  | Тур. | Max. | Unit  |
| Total gate-charge                                  | V <sub>DS</sub> =30V                                     | Q <sub>G</sub>      | -     | 20   | -    |       |
| Gate to source charge                              | V <sub>GS</sub> =10V                                     | Q <sub>GS</sub>     | -     | 3.1  | -    | nC    |
| Gate to drain (Miller) charge                      | I <sub>D</sub> =4.0A                                     | Q <sub>GD</sub>     | -     | 3.2  | -    |       |
| Source-drain diode characteristics                 |  |                     |       |      |      |       |
| Characteristic                                     | Test condition   | Symbol              | Value |      |      | Unit  |
| Characteristic                                     | lest condition   | Symbol              | Min.  | Тур. | Max. | Oiiit |
| Diode forward voltage <sup>3)</sup>                | I <sub>SD</sub> =4.0A, V <sub>GS</sub> =0V               | V <sub>SD</sub>     | -     | -    | 1.2  | V     |
| Source-drain current (body diode)                  |  | I <sub>SD</sub>     | -     | -    | 4.0  | Α     |

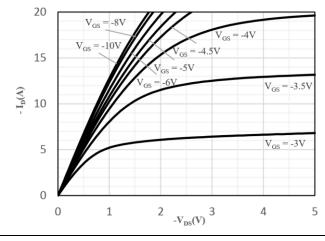
- Reja, is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rejic is guaranteed by design while Rec. is determined by the user's board design. a)  $78^{\circ}\text{C/W}$  when mounted on a  $1\text{in}^2$  pad of 2oz copper on FR-4 board b)  $100^{\circ}\text{C/W}$  when mounted on a minimum pad
- Repetitive rating: pulse width limited by maximum junction temper Pulse test: pulse width ≤300μs, duty cycle ≤2%
- 2) 3)
- Guaranteed by design, not subject to production

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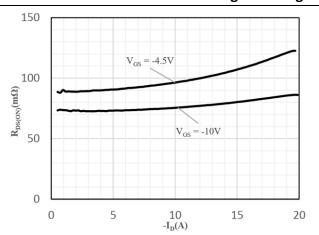




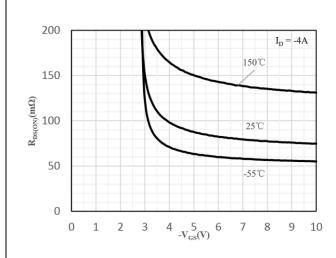
## **Output characteristics**



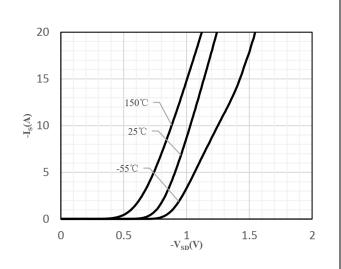
#### On-resistance vs. drain current and gate voltage



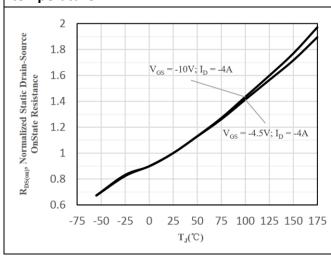
#### ON-resistance vs. gate-source voltage



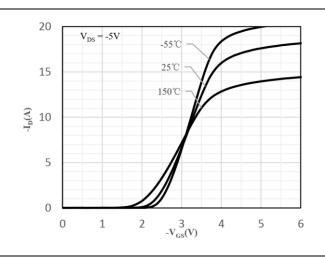
**Body-diode characteristics** 



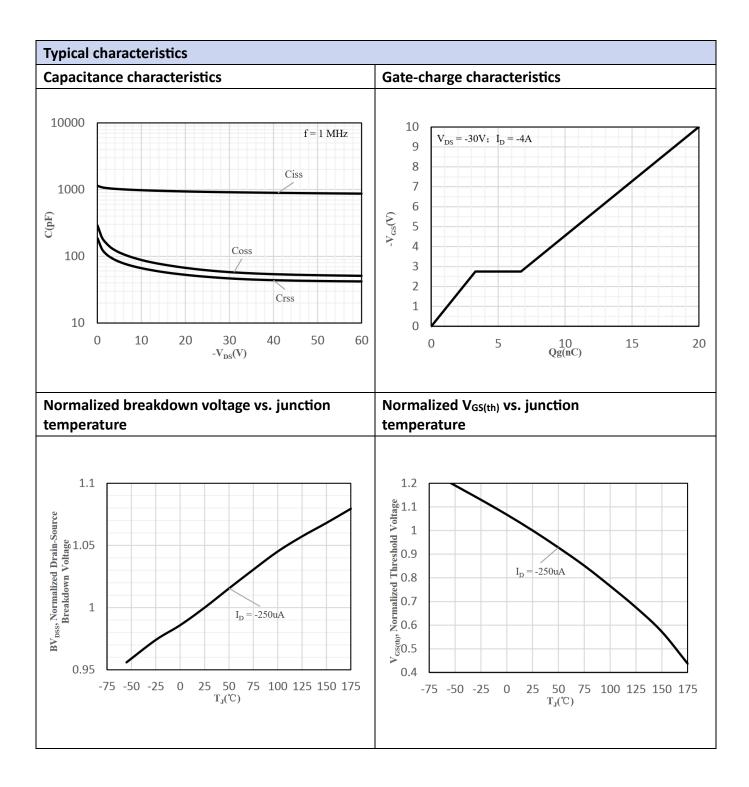
# Normalized ON-resistance vs. junction temperature



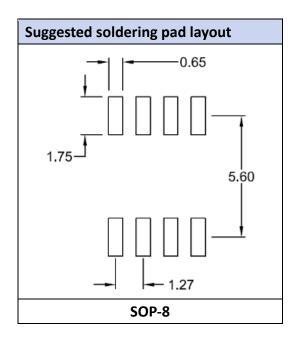
#### **Transfer characteristics**











| Ordering information |         |         |                        |            |  |  |
|----------------------|---------|---------|------------------------|------------|--|--|
| Part Number          | Marking | Package | Shipping Quantity      | Dimensions |  |  |
| AKS4P06-S8           | 4P06    | SOP-8   | 4000 pcs / tape & reel |            |  |  |

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